SPICE Device Model SQJ463EP



Vishay Siliconix

P-Channel 40 V (D-S) MOSFET

DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

 This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	1.4	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -18 \text{ A}$	0.008	0.007	Ω
		V_{GS} = - 4.5 V, I _D = - 15 A	0.013	0.011	
Forward Transconductance ^a	g fs	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -18 \text{ A}$	42	45	S
Diode Forward Voltage	V _{SD}	I _S = - 4.5 A	- 0.70	- 0.80	V
Dynamic ^b					
Input Capacitance	C _{iss}	V_{DS} = - 20 V, V_{GS} = 0 V, f = 1 MHz	4760	4700	pF
Output Capacitance	C _{oss}		700	625	
Reverse Transfer Capacitance	C _{rss}		400	460	
Total Gate Charge	Qg	V_{DS} = - 20 V, V_{GS} = - 10 V, I_D = - 18.6 A	95	97	nC
Gate-Source Charge	Q _{gs}		14	14	
Gate-Drain Charge	Q _{gd}		23	23	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

• Dots and squares represent measured data.

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